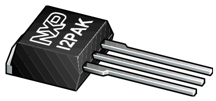


PSMN7R8-120ES

N-channel 120 V 7.9 mΩ standard level MOSFET in I2PAK

18 February 2013 Product data sheet

1. General description

Standard level N-channel MOSFET in I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic power supply equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Improved dynamic avalanche performance
- Suitable for standard level gate drive
- I2PAK package for slimline adaptors & height constrained applications

3. Applications

- AC-to-DC power supply
- Synchronous rectification
- Motor control
- Slimline adaptors & chargers

4. Quick reference data

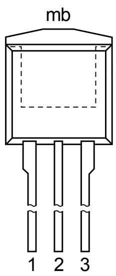
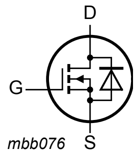
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	120	V
I_D	drain current	$T_{mb} = 25$ °C; $V_{GS} = 10$ V; Fig. 1		-	-	70	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; Fig. 2		-	-	349	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10$ V; $I_D = 25$ A; $T_j = 25$ °C; Fig. 12		4.7	6.72	7.9	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 10$ V; $I_D = 25$ A; $V_{DS} = 60$ V; Fig. 14; Fig. 15		-	50.5	-	nC
$Q_{G(tot)}$	total gate charge			-	167	-	nC
Avalanche ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; $I_D = 70$ A; $V_{sup} \leq 120$ V; unclamped; $R_{GS} = 50$ Ω; Fig. 3		-	-	386	mJ

Scan or click this QR code to view the latest information for this product

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 I2PAK (SOT226)	
2	D	drain		
3	S	source		
mb	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN7R8-120ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN7R8-120ES	PSMN7R8-120ES

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	120	V
V_{DGR}	drain-gate voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C; R_{GS} = 20 kΩ		-	120	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 1		-	70	A
		V_{GS} = 10 V; T_{mb} = 100 °C; Fig. 1		-	70	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C; Fig. 4		-	280	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	349	W
T_{stg}	storage temperature			-55	175	°C

Symbol	Parameter	Conditions		Min	Max	Unit
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C		-	70	A
I_{SM}	peak source current	pulsed; $t_p \leq$ 10 µs; T_{mb} = 25 °C		-	280	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 70 A; $V_{sup} \leq$ 120 V; unclamped; R_{GS} = 50 Ω; Fig. 3		-	386	mJ

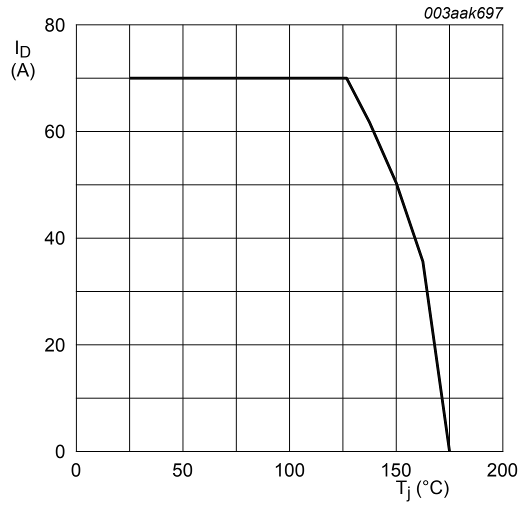


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10 V$$

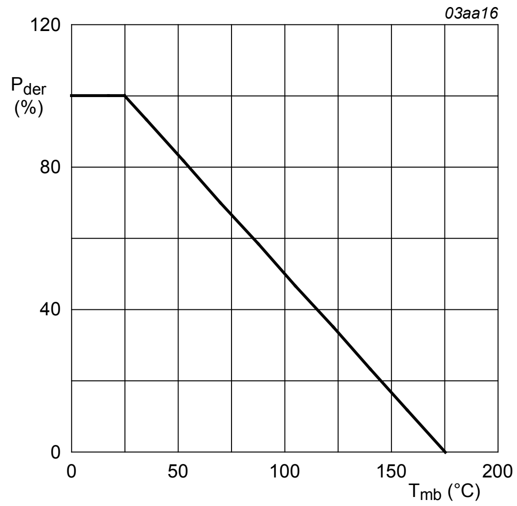


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\,\%$$

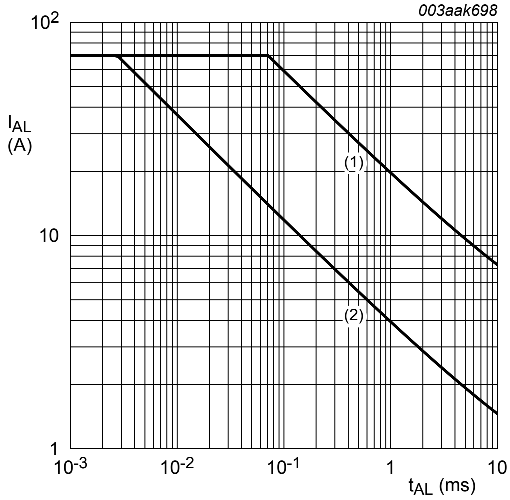


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

(1) Single-pulse; $T_j = 25\,°C$.

(2) Single-pulse; $T_j = 125\,°C$.

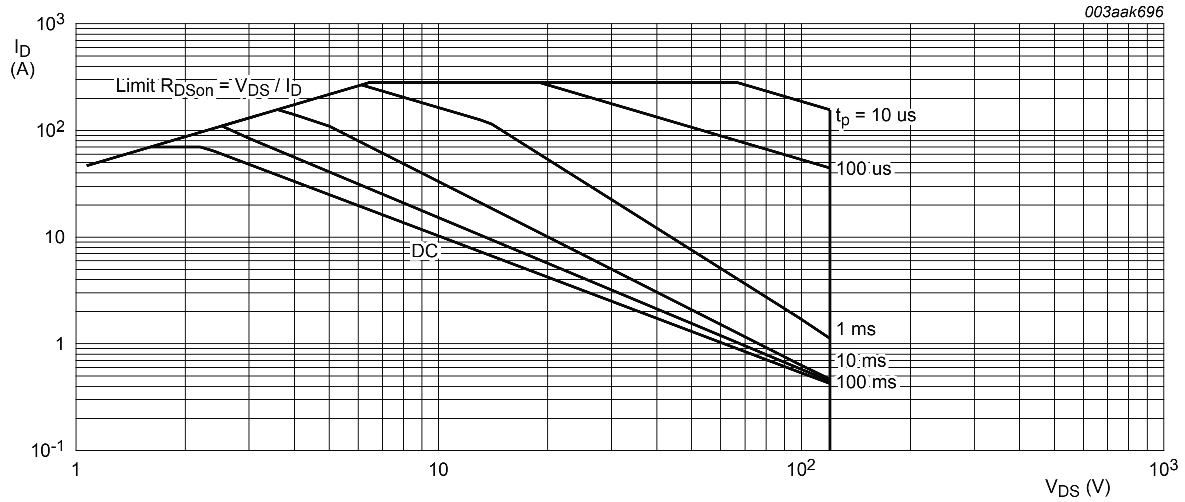


Fig. 4. Safe operating area; continuous and peak drain current as a function of drain-source voltage

$T_{mb} = 25\,°C$; I_{DM} is single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	0.35	0.43	K/W

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air		-	65	-	K/W

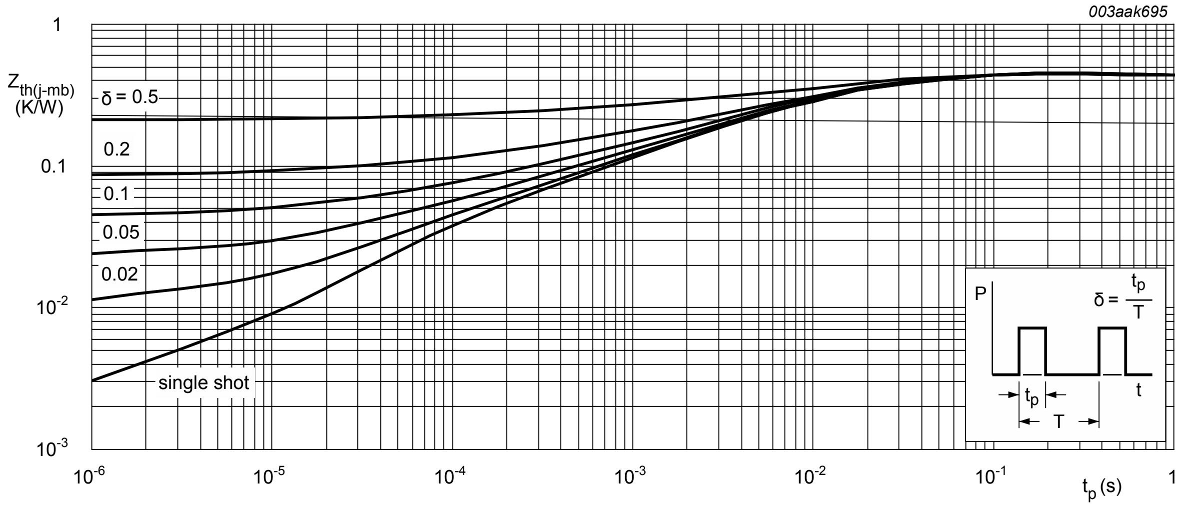


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		120	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		108	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 10; Fig. 11		2	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 10		1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 10		-	-	4.6	V
I_{DSS}	drain leakage current	V_{DS} = 120 V; V_{GS} = 0 V; T_j = 25 °C		-	0.1	1	µA
		V_{DS} = 120 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	10	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 12		4.7	6.72	7.9	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 12; Fig. 13		-	19.4	22.9	mΩ

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R_G	internal gate resistance (AC)	f = 1 MHz		0.39	0.78	1.56	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 60 V; V_{GS} = 10 V; Fig. 14; Fig. 15		-	167	-	nC
Q_{GS}	gate-source charge			-	36.9	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge			-	24.2	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge			-	12.7	-	nC
Q_{GD}	gate-drain charge			-	50.5	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 25 A; V_{DS} = 60 V; Fig. 14; Fig. 15		-	4.5	-	V
C_{iss}	input capacitance	V_{DS} = 60 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; Fig. 16		-	9473	-	pF
C_{oss}	output capacitance			-	441	-	pF
C_{rss}	reverse transfer capacitance			-	298	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 60 V; R_L = 2.4 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω; T_j = 25 °C		-	45.5	-	ns
t_r	rise time			-	55.3	-	ns
$t_{d(off)}$	turn-off delay time			-	151.8	-	ns
t_f	fall time			-	60.8	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 17		-	0.81	1.2	V
t_{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 60 V		-	75.7	-	ns
Q_r	recovered charge			-	264	-	nC

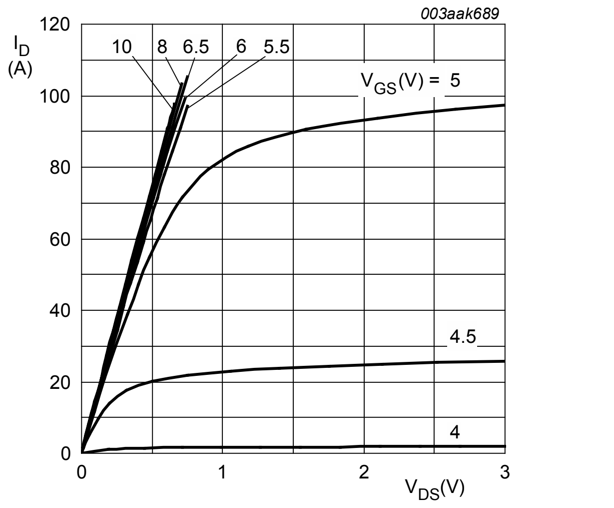


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25\,°C$

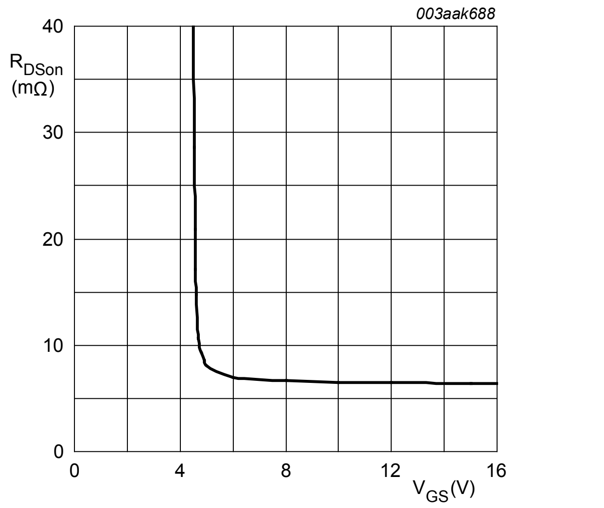


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\,°C$

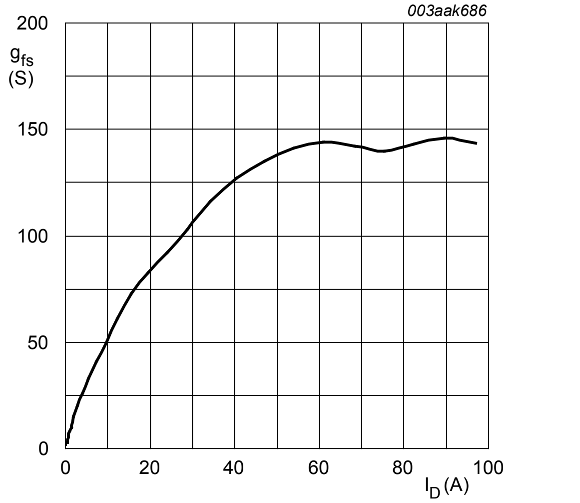


Fig. 8. Forward transconductance as a function of drain current; typical values

$T_j = 25\,°C; V_{DS} = 10\,V$

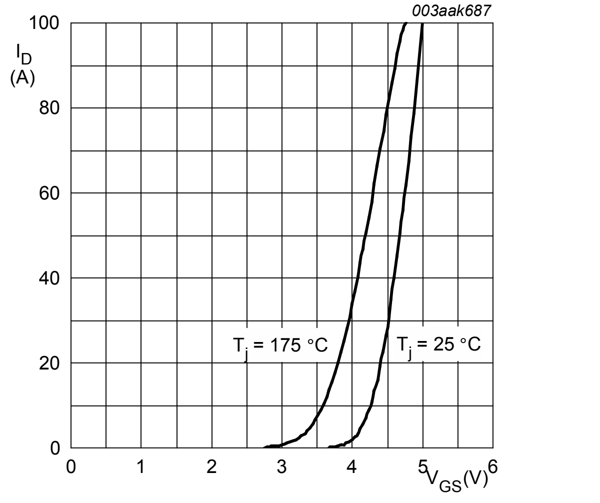


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} > I_D \times R_{DSon}$

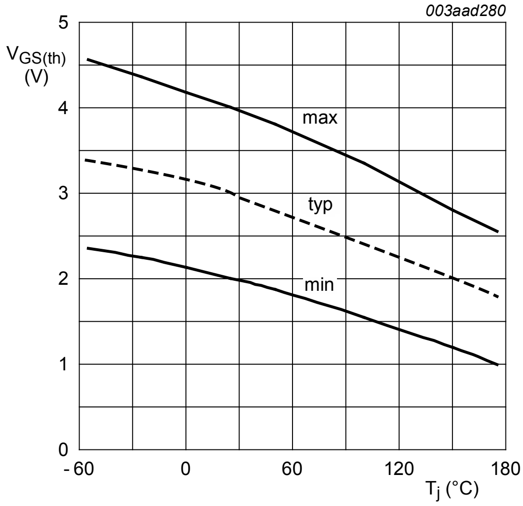


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\ \text{mA};\ V_{DS} = V_{GS}$

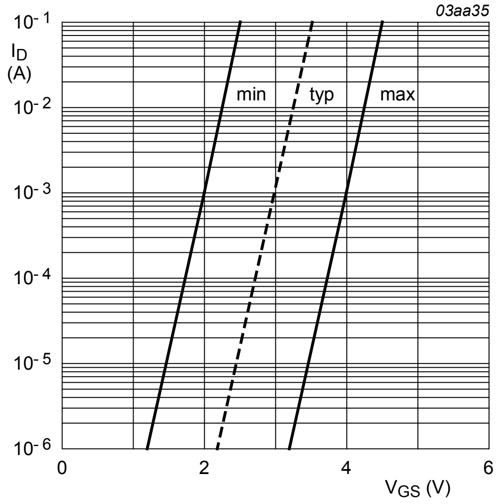


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25\,°C;\ V_{DS} = 5V$

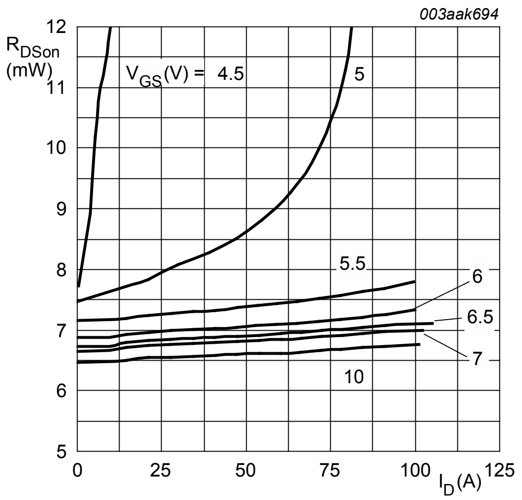


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25\,°C$

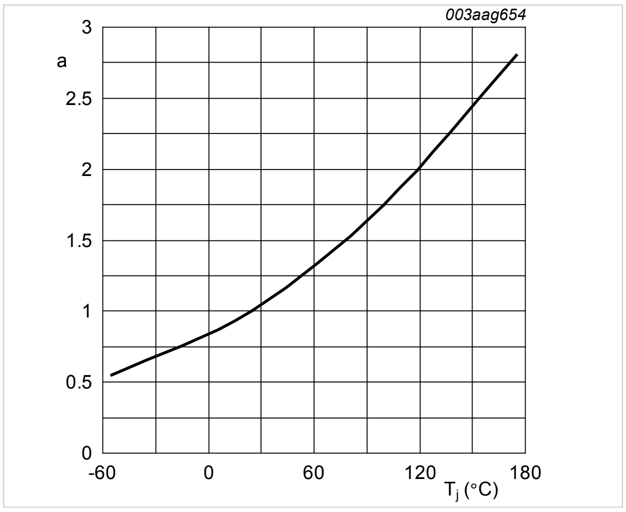


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

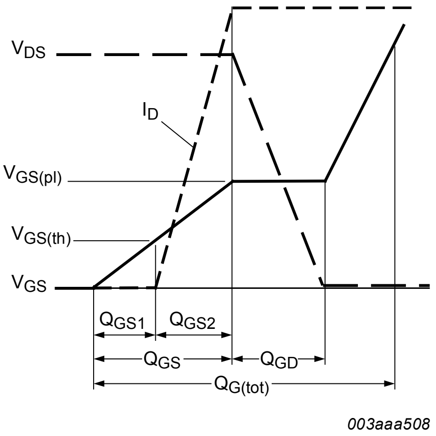


Fig. 14. Gate charge waveform definitions

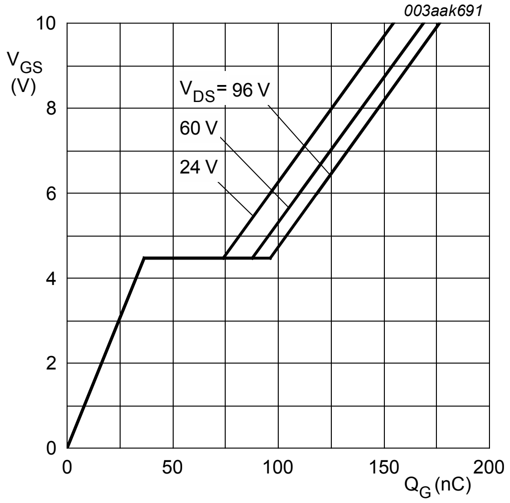


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25\,°C; I_D = 25\,A$

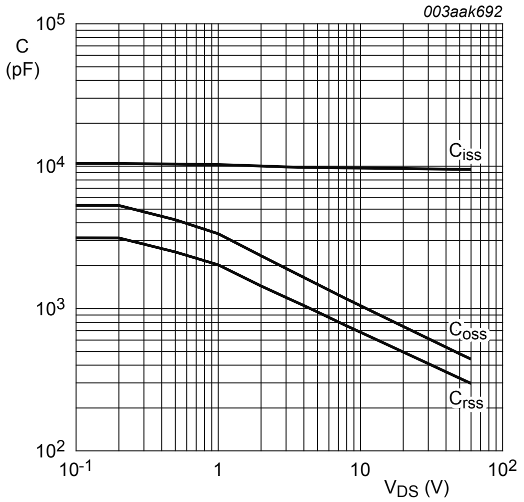


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\,V; f = 1\,MHz$

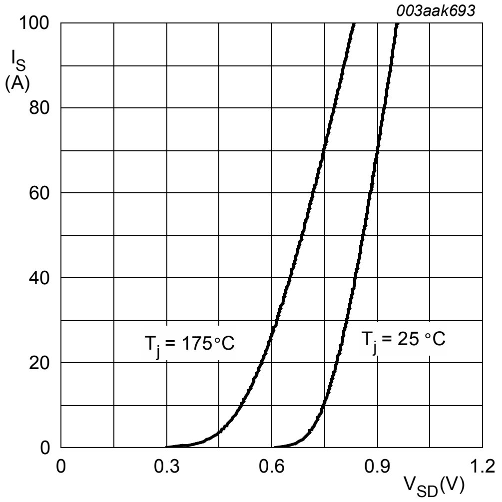
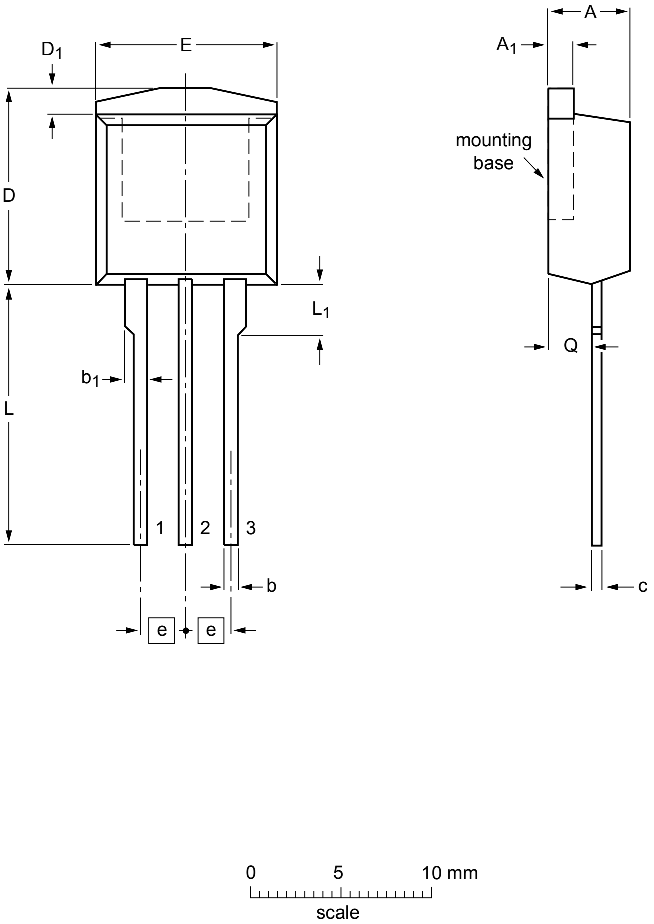


Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0\,V$

11. Package outline

Plastic single-ended package (I2PAK); low-profile 3-lead TO-262 **SOT226**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1	c	D max	D_1	E	e	L	L_1	Q
mm	4.5 4.1	1.40 1.27	0.85 0.60	1.3 1.0	0.7 0.4	11	1.6 1.2	10.3 9.7	2.54	15.0 13.5	3.30 2.79	2.6 2.2

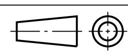
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT226		TO-262				~~06-02-14~~ 09-08-25

Fig. 18. Package outline I2PAK (SOT226)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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